

	<b>Typ e</b>	<b>Hits</b>	<b>Search Text</b>	<b>DBs</b>	<b>Time Stamp</b>	<b>Comment s</b>	<b>Error Definit ion</b>
1	BRS	2558	(high with dielectric) and (aluminum or Al) and (zirconium or Zr) and (hafnium or Hf)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/2 1 14:11		
2	BRS	1769	((high with dielectric) and (aluminum or Al) and (zirconium or Zr) and (hafnium or Hf)) and nitrid\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/1 8 12:49		
3	BRS	1521	((high with dielectric) and (aluminum or Al) and (zirconium or Zr) and (hafnium or Hf)) and nitrid\$5) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/1 8 12:49		
4	BRS	1314	((high with dielectric) and (aluminum or Al) and (zirconium or Zr) and (hafnium or Hf)) and nitrid\$5) and semiconductor) and (dielectric with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/1 8 13:00		

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5 BRS 134		(((((high with dielectric) and (aluminum or Al) and (zirconium or Zr) and (hafnium or Hf)) and nitrid\$5) and semiconductor) and (dielectric with layer)) and (composite with dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/1 8 16:37		
6 BRS 6		(nitridation with (zirconium adj oxide) and (high with dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/1 8 14:35		
7 IS& R 1		("6251761").PN.	USPAT	2004/06/1 8 16:37		
8 BRS 8773		438/183,197,199,216,217,229-231,240,257,261-263,266,287,584,591,592,761,770,785,787.ccls .	USPAT; US-PGPUB	2004/06/2 1 14:15		
9 BRS 348		438/183,197,199,216,217,229-231,240,257,261-263,266,287,584,591,592,761,770,785,787.ccls . and (high-K with dielectric)	USPAT; US-PGPUB	2004/06/2 1 14:15		

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10	BRS	331	(438/183,197,199,216,217,229-231,240,257,261-263,266,287,584,591,592,761,770,785,787.ccl s. and (high-K with dielectric)) and nitr\$6	USPAT; US-PGPUB	2004/06/2 1 14:17		